

## N-channel 650 V, 0.024 $\Omega$ typ., 84 A, MDmesh™ V Power MOSFET in TO-247 and TO-247 long leads packages

Datasheet - production data

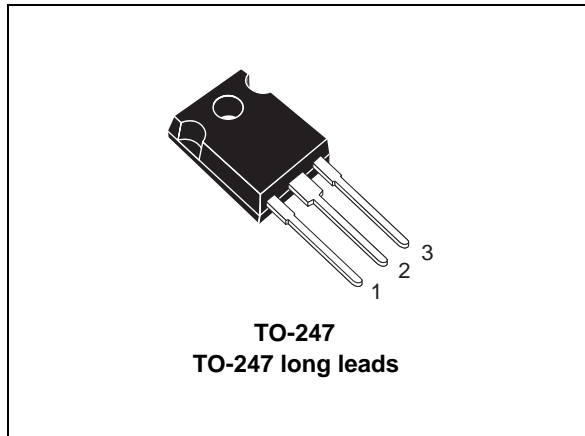
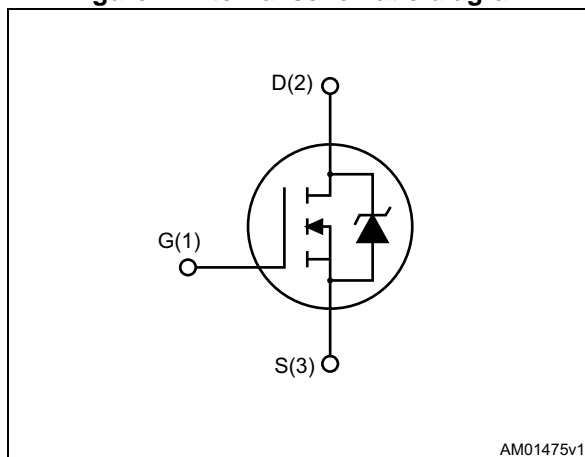


Figure 1. Internal schematic diagram



### Features

Order codes	$V_{DSS}$ @ $T_{jmax.}$	$R_{DS(on)}$ max.	$I_D$
STW88N65M5	710 V	< 0.029 $\Omega$	84 A
STWA88N65M5			

- Worldwide best  $R_{DS(on)}$  in TO-247
- Higher  $V_{DSS}$  rating
- Higher dv/dt capability
- Excellent switching performance
- Easy to drive
- 100% avalanche tested

### Applications

- High efficiency switching applications:
  - Servers
  - PV inverters
  - Telecom infrastructure
  - Multi kW battery chargers

### Description

These devices are N-channel MDmesh™ V Power MOSFETs based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

Table 1. Device summary

Order codes	Marking	Packages	Packaging
STW88N65M5	88N65M5	TO-247	Tube
STWA88N65M5		TO-247 long leads	

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate- source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	84	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	50.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	336	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	450	W
$I_{AR}$	Max current during repetitive or single pulse avalanche (pulse width limited by $T_{JMAX}$ )	15	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	2000	mJ
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$T_{stg}$	Storage temperature	- 55 to 150	$^\circ\text{C}$
$T_j$	Max. operating junction temperature	150	$^\circ\text{C}$

1. Pulse width limited by safe operating area

2.  $I_{SD} \leq 84\text{ A}$ ,  $di/dt = 400\text{ A}/\mu\text{s}$ , peak  $V_{DS} < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.28	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	50	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	650			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 650\text{ V}$ $V_{DS} = 650\text{ V}$ , $T_C = 125\text{ °C}$			1 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 25\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 42\text{ A}$		0.024	0.029	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	8825	-	pF
$C_{oss}$	Output capacitance			223		pF
$C_{rss}$	Reverse transfer capacitance			11		pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{GS} = 0$ , $V_{DS} = 0\text{ to }520\text{ V}$	-	778	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related	$V_{GS} = 0$ , $V_{DS} = 0\text{ to }520\text{ V}$	-	202	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.79	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}$ , $I_D = 42\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 16</a> )	-	204	-	nC
$Q_{gs}$	Gate-source charge			51		nC
$Q_{gd}$	Gate-drain charge			84		nC

- $C_{o(tr)}$  is a constant capacitance value that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- $C_{o(er)}$  is a constant capacitance value that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(V)}$	Voltage delay time	$V_{DD} = 400\text{ V}$ , $I_D = 56\text{ A}$ ,		141		ns
$t_{r(V)}$	Voltage rise time	$R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$		16		ns
$t_{f(i)}$	Current fall time	(see <a href="#">Figure 17</a> )	-	29	-	ns
$t_{c(off)}$	Crossing time	(see <a href="#">Figure 20</a> )		56		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current				84	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		336	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 84\text{ A}$ , $V_{GS} = 0$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 84\text{ A}$ ,		544		ns
$Q_{rr}$	Reverse recovery charge	$di/dt = 100\text{ A}/\mu\text{s}$	-	14		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	$V_{DD} = 100\text{ V}$ (see <a href="#">Figure 17</a> )		50		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 84\text{ A}$ ,		660		ns
$Q_{rr}$	Reverse recovery charge	$di/dt = 100\text{ A}/\mu\text{s}$	-	20		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	$V_{DD} = 100\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 17</a> )		60		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

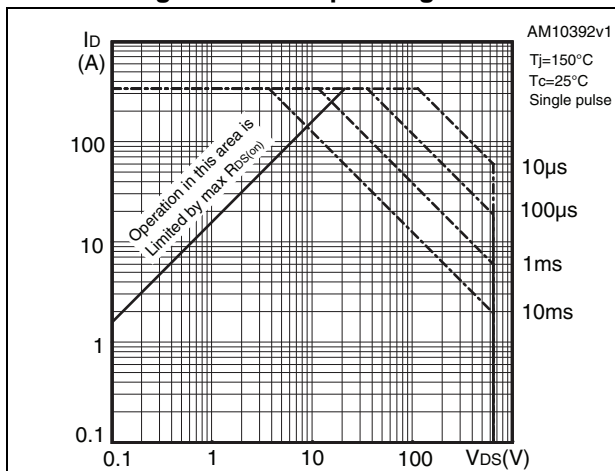


Figure 3. Thermal impedance

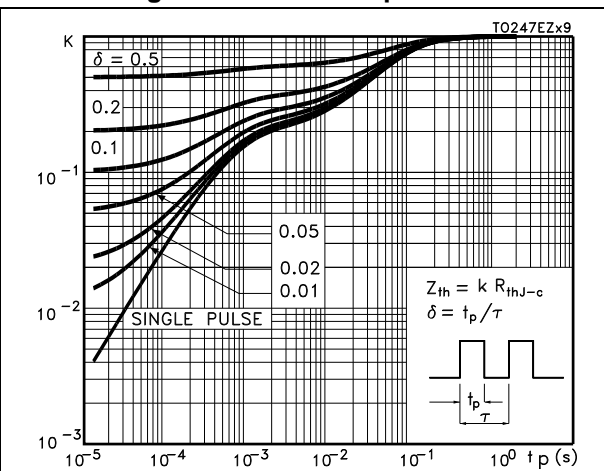


Figure 4. Output characteristics

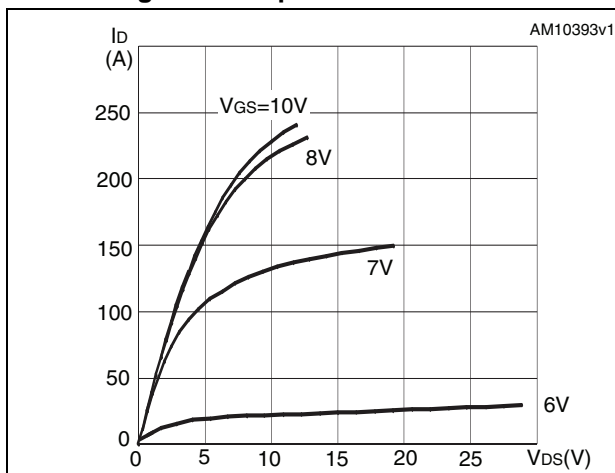


Figure 5. Transfer characteristics

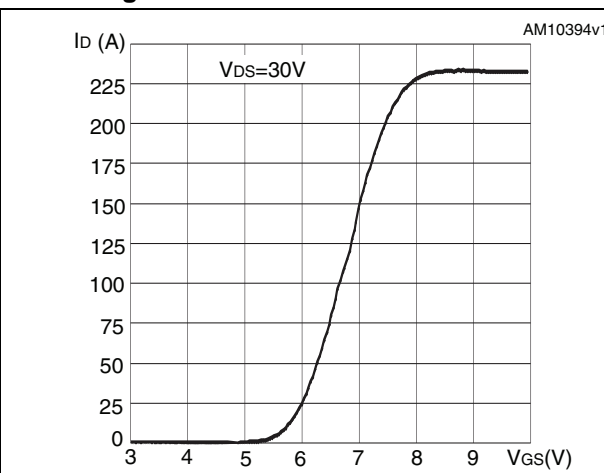


Figure 6. Gate charge vs gate-source voltage

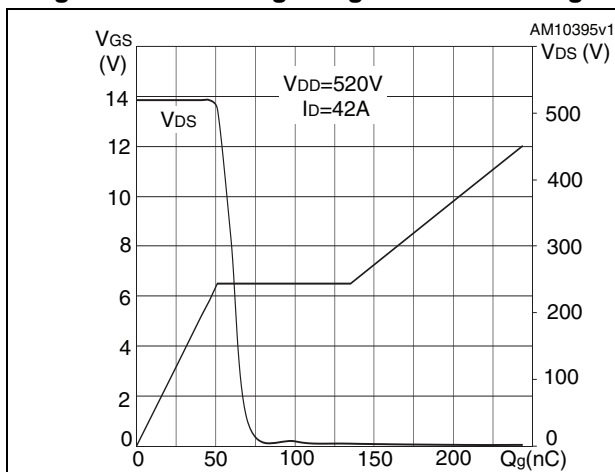


Figure 7. Static drain-source on resistance

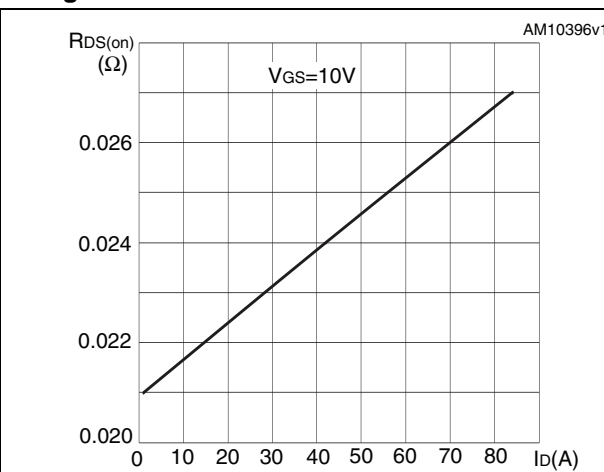


Figure 8. Capacitance variations

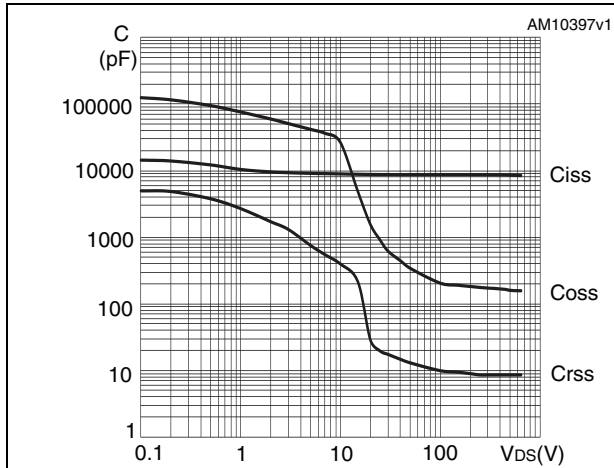


Figure 9. Output capacitance stored energy

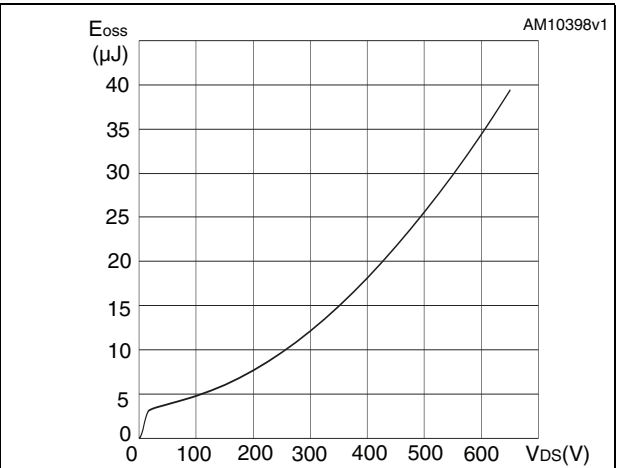


Figure 10. Normalized gate threshold voltage vs temperature

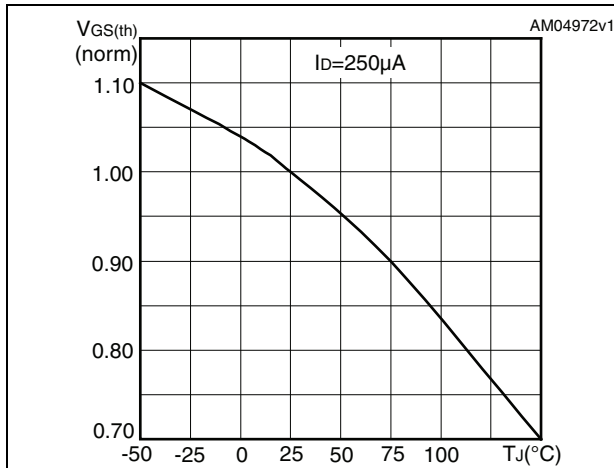


Figure 11. Normalized on resistance vs temperature

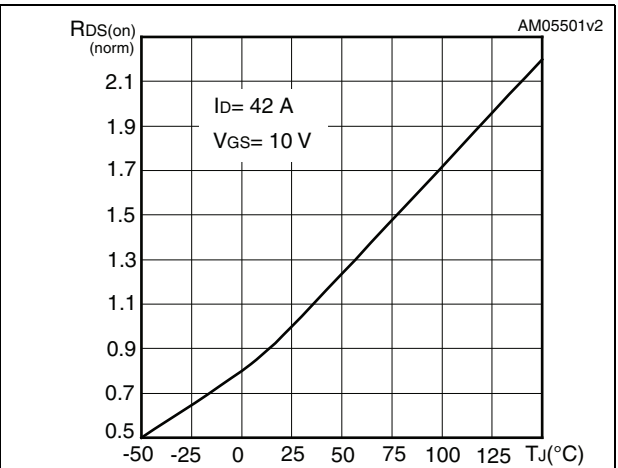


Figure 12. Source-drain diode forward characteristics

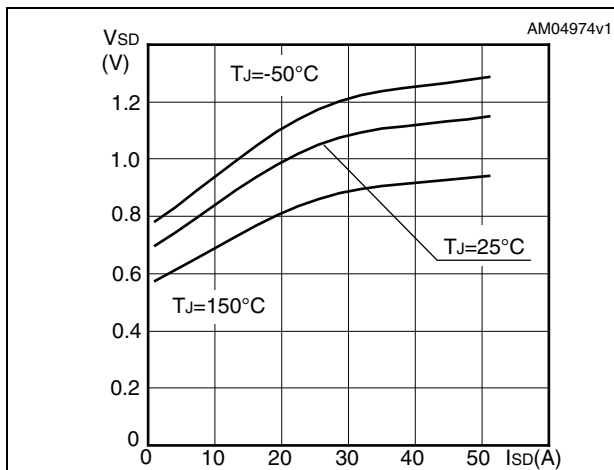


Figure 13. Normalized V<sub>DS</sub> vs temperature

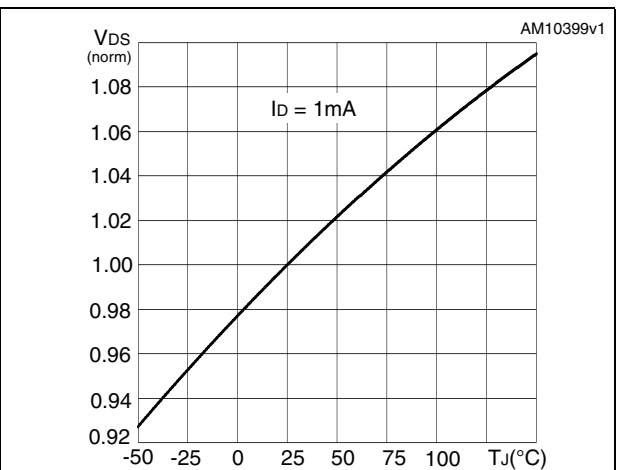
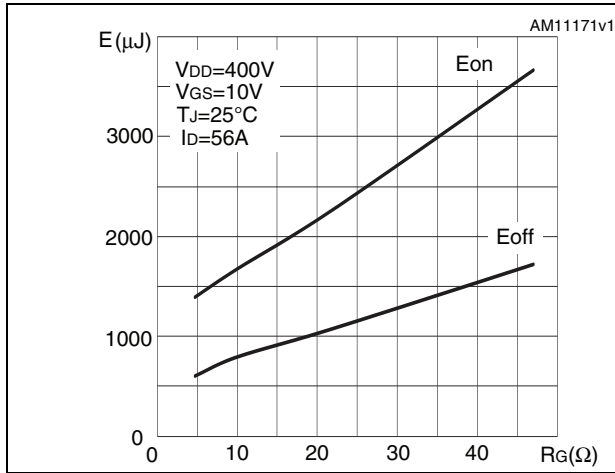


Figure 14. Switching losses vs gate resistance  
(1)



1.  $E_{on}$  including reverse recovery of a SiC diode



### 3 Test circuits

Figure 15. Switching times test circuit for resistive load

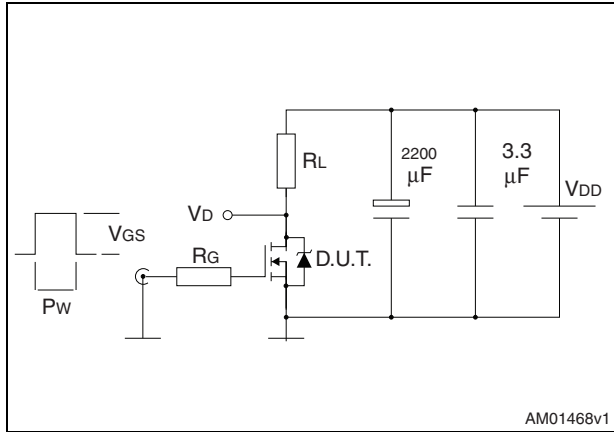


Figure 16. Gate charge test circuit

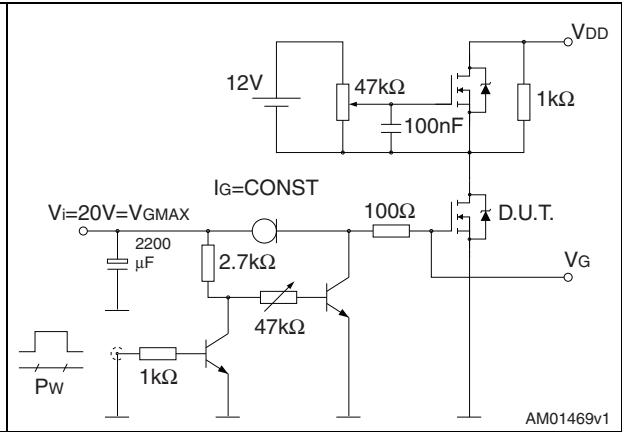


Figure 17. Test circuit for inductive load switching and diode recovery times

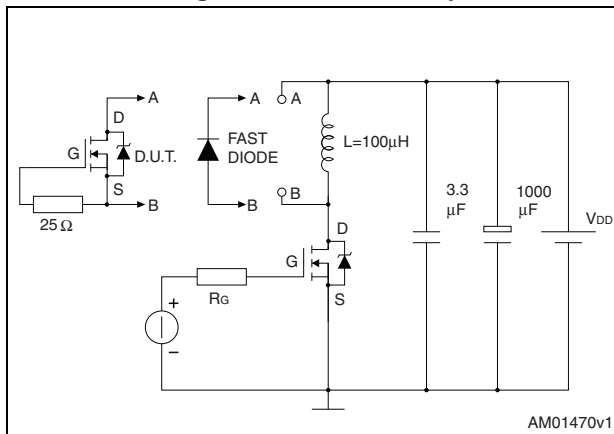


Figure 18. Unclamped inductive load test circuit

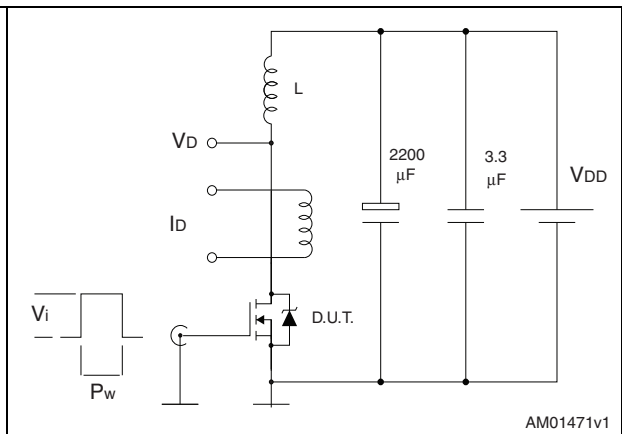


Figure 19. Unclamped inductive waveform

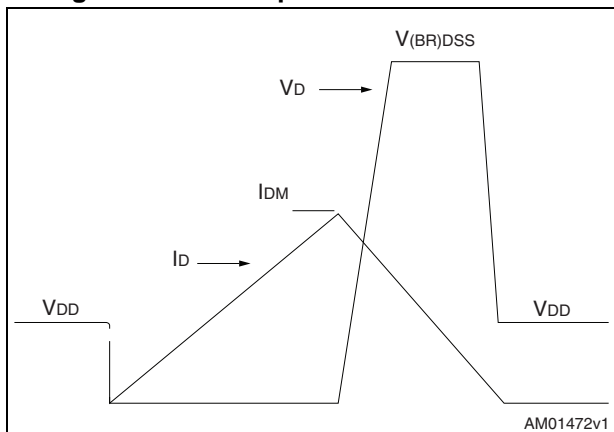
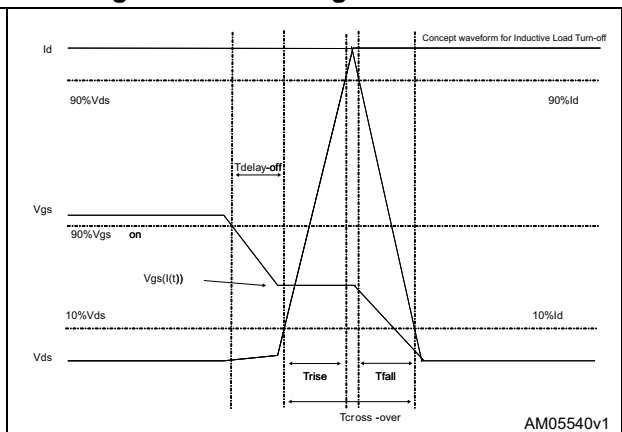


Figure 20. Switching time waveform



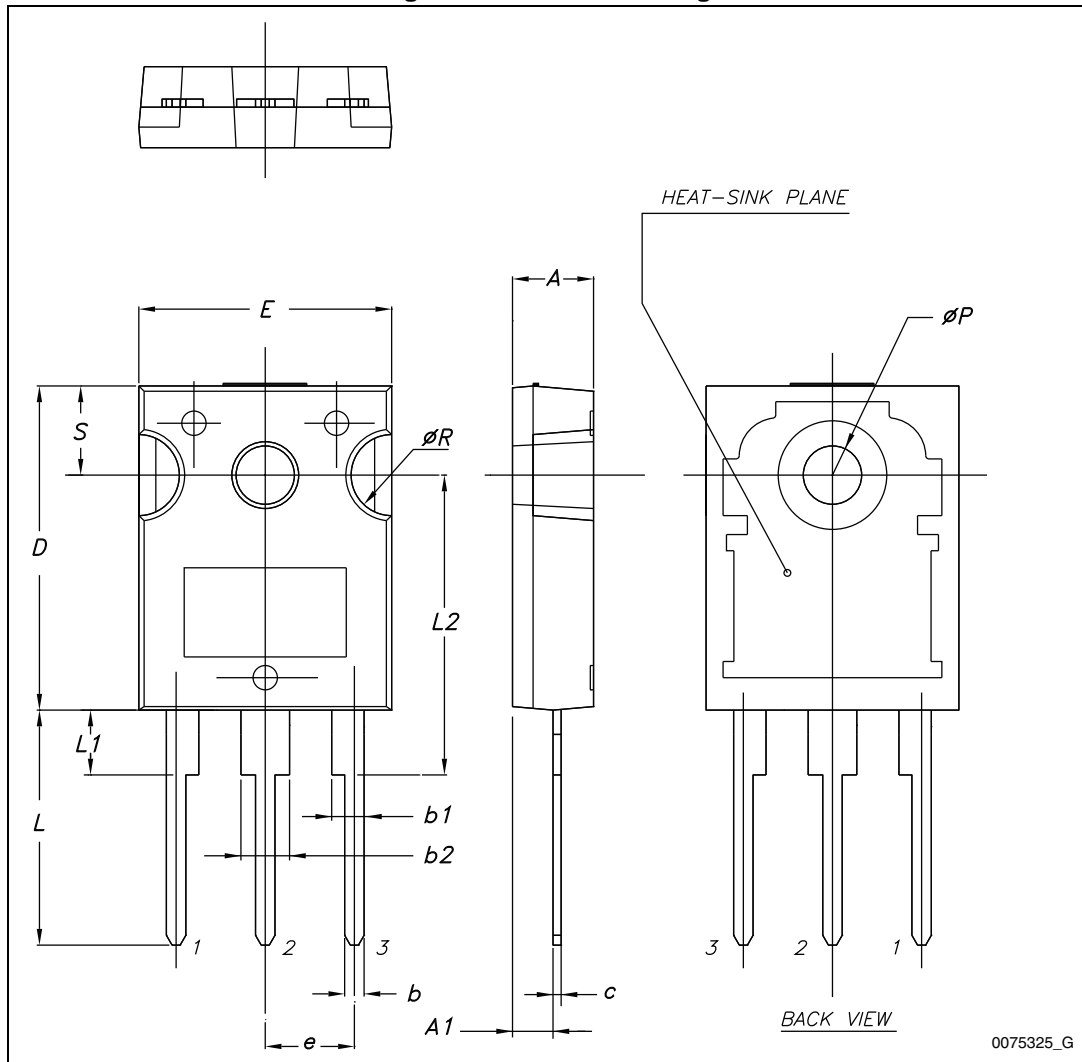
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**Table 8. TO-247 mechanical data**

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Figure 21. TO-247 drawing

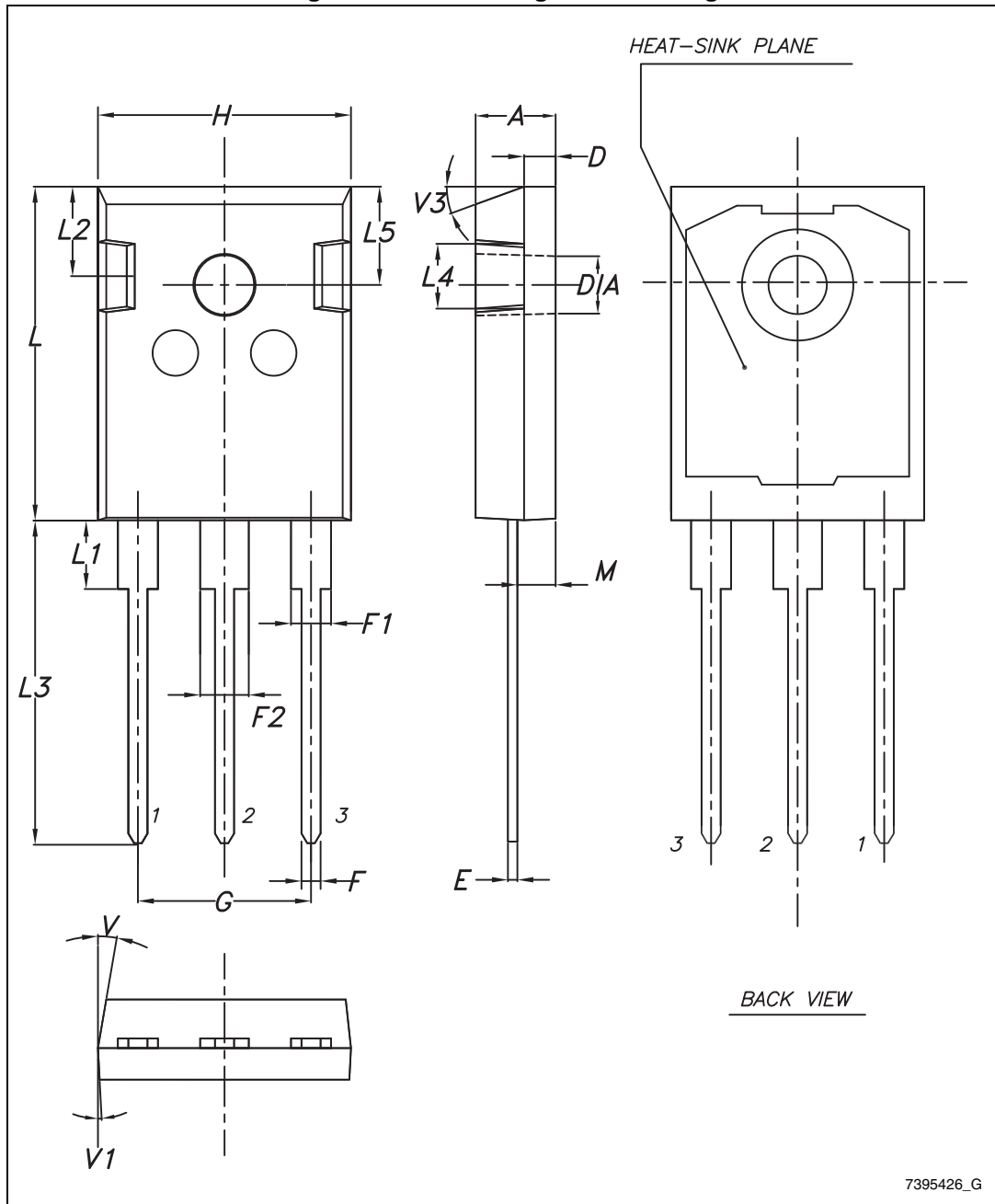


0075325\_G

Table 9. TO-247 long leads mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.90		5.15
D	1.85		2.10
E	0.55		0.67
F	1.07		1.32
F1	1.90		2.38
F2	2.87		3.38
G	10.90 BSC		
H	15.77		16.02
L	20.82		21.07
L1	4.16		4.47
L2	5.49		5.74
L3	20.05		20.30
L4	3.68		3.93
L5	6.04		6.29
M	2.25		2.55
V		10°	
V1		3°	
V3		20°	
Dia.	3.55		3.66

Figure 22. TO-247 long leads drawing



## 5 Revision history

Table 10. Document revision history

Date	Revision	Changes
23-Nov-2011	1	First release.
09-Dec-2011	2	Document status promoted from preliminary data to datasheet.
12-Jun-2012	3	Updated title on the coverpage.
30-Nov-2012	4	Added new part number: STWA88N65M5 Updated: <a href="#">Section 4: Package mechanical data</a>

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